



W24257A

32K × 8 HIGH SPEED CMOS STATIC RAM

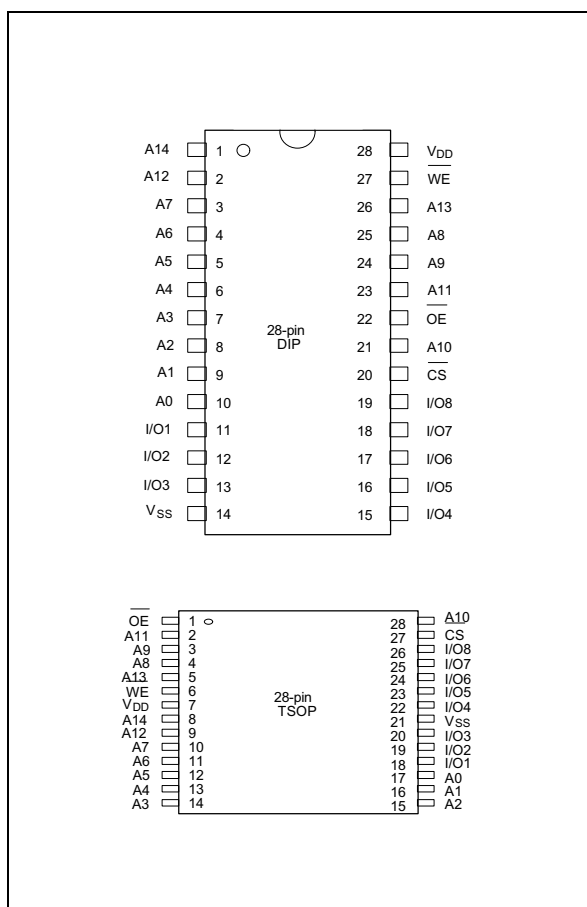
GENERAL DESCRIPTION

The W24257A is a high speed, low power CMOS static RAM organized as 32768 × 8 bits that operates on a single 5-volt power supply. This device is manufactured using Winbond's high performance CMOS technology.

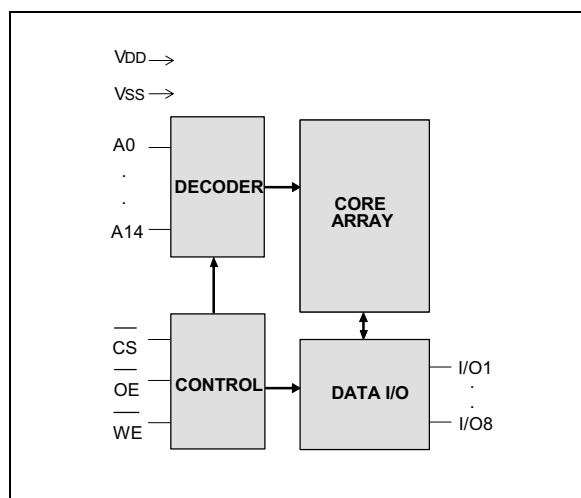
FEATURES

- High speed access time: 10/12/15/20 nS (max.)
- Low power consumption:
 - Active: 400 mW (typ.)
- Single +5V power supply
- Fully static operation
- All inputs and outputs directly TTL compatible
- Three-state outputs
- Available packages: 28-pin 300 mil SOJ, 330 mil SOP, skinny DIP and standard type one TSOP (8 mm × 13.4 mm)

PIN CONFIGURATIONS



BLOCK DIAGRAM



PIN DESCRIPTION

SYMBOL	DESCRIPTION
A0–A14	Address Inputs
I/O1–I/O8	Data Inputs/Outputs
$\overline{CS}$	Chip Select Input
$\overline{WE}$	Write Enable Input
$\overline{OE}$	Output Enable Input
VDD	Power Supply
VSS	Ground



DC CHARACTERISTICS

Absolute Maximum Ratings

PARAMETER	RATING	UNIT
Supply Voltage to Vss Potential	-0.5 to +7.0	V
Input/Output to Vss Potential	-0.5 to V _{DD} +0.5	V
Allowable Power Dissipation	1.0	W
Storage Temperature	-65 to +150	°C
Operating Temperature	0 to +70	°C

Note: Exposure to conditions beyond those listed under Absolute Maximum Ratings may adversely affect the life and reliability of the device.

TRUTH TABLE

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	MODE	I/O1–I/O8	V _{DD} CURRENT
H	X	X	Not Selected	High Z	I _{SB} , I _{SB1}
L	H	H	Output Disable	High Z	I _{DD}
L	L	H	Read	Data Out	I _{DD}
L	X	L	Write	Data In	I _{DD}

OPERATING CHARACTERISTICS

(V_{DD} = 5V ±10%, V_{SS} = 0V, T_A = 0 to 70° C)

PARAMETER	SYM.	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Input Low Voltage	V _{IL}	-	-0.5	-	+0.8	V
Input High Voltage	V _{IH}	-	+2.2	-	V _{DD} +0.5	V
Input Leakage Current	I _{LI}	V _{IN} = V _{SS} to V _{DD}	-10	-	+10	μA
Output Leakage Current	I _{LO}	V _{I/O} = V _{SS} to V _{DD} , $\overline{CS}$ = V _{IH} or $\overline{OE}$ = V _{IH} or $\overline{WE}$ = V _{IL}	-10	-	+10	μA
Output Low Voltage	V _{OL}	I _{OL} = +8.0 mA	-	-	0.4	V
Output High Voltage	V _{OH}	I _{OH} = -4.0 mA	2.4	-	-	V
Operating Power Supply Current	I _{DD}	$\overline{CS}$ = V _{IL} , I/O = 0 mA Cycle = MIN Duty = 100%	10	-	-	170 mA
			12	-	-	160 mA
			15	-	-	150 mA
			20	-	-	140 mA
Standby Power Supply Current	I _{SB}	$\overline{CS}$ = V _{IH} Cycle = MIN, Duty = 100%	-	-	30	mA
	I _{SB1}	$\overline{CS}$ ≥ V _{DD} -0.2V	-	-	10	mA

Note: Typical characteristics are at V_{DD} = 5V, T_A = 25° C.

**CAPACITANCE**(V_{DD} = 5V, T_A = 25° C, f = 1 MHz)

PARAMETER	SYM.	CONDITIONS	MAX.	UNIT
Input Capacitance	C _{IN}	V _{IN} = 0V	8	pF
Input/Output Capacitance	C _{I/O}	V _{OUT} = 0V	10	pF

Note: These parameters are sampled but not 100% tested.

THERMAL RESISTANCE

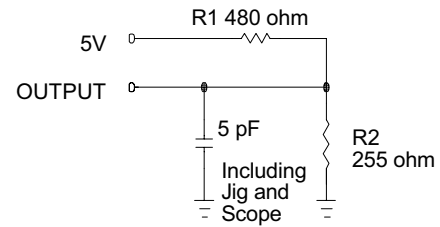
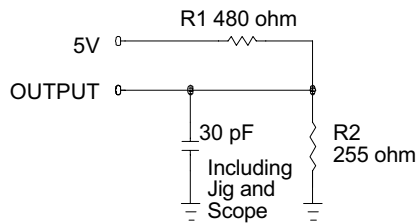
PARAMETER	SYM	CONDITIONS	MAX.	UNIT
Junction to Case Thermal Resistance	θ_{JC}	A. F. R. = 1m/sec, T _A = 25° C	20	°C/W
Junction to Ambient Thermal Resistance	θ_{JA}	A. F. R. = 1m/sec, T _A = 25° C	60	°C/W

Note: These parameters are only applied to "TSOP" and "SOJ" package types.

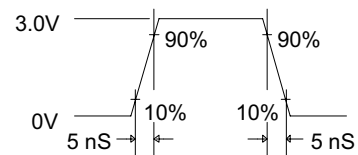
AC TEST CONDITIONS

PARAMETER	CONDITIONS
Input Pulse Levels	0V to 3V
Input Rise and Fall Times	5 nS
Input and Output Timing Reference Level	1.5V
Output Load	C _L = 30 pF, I _{OH} /I _{OL} = -4 mA/8 mA

AC TEST LOADS AND WAVEFORM



(For T_{CLZ} , T_{OLZ} , T_{CHZ} , T_{OHZ} , T_{WHZ} , T_{OW})



AC CHARACTERISTICS

(V_{DD} = 5V ±10%, V_{SS} = 0V, T_A = 0 to 70° C)

Read Cycle

PARAMETER	SYM.	W24257A-10		W24257A-12		W24257A-15		W24257A-20		UNIT
		MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Read Cycle Time	T _{RC}	10	-	12	-	15	-	20	-	nS
Address Access Time	T _{AA}	-	10	-	12	-	15	-	20	nS
Chip Select Access Time	T _{ACS}	-	10	-	12	-	15	-	20	nS
Output Enable to Output Valid	T _{AOE}	-	5	-	6	-	7	-	10	nS
Chip Selection to Output in Low Z	T _{CLZ} *	3	-	3	-	3	-	3	-	nS
Output Enable to Output in Low Z	T _{OLZ} *	0	-	0	-	0	-	0	-	nS
Chip Deselection to Output in High Z	T _{CHZ} *	-	5	-	6	-	7	-	10	nS
Output Disable to Output in High Z	T _{OHZ} *	-	5	-	6	-	7	-	10	nS
Output Hold from Address Change	T _{OH}	3	-	3	-	3	-	3	-	nS

* These parameters are sampled but not 100% tested.

Write Cycle

PARAMETER		SYM.	W24257A-10		W24257A-12		W24257A-15		W24257A-20		UNIT
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Write Cycle Time		T _{WC}	10	-	12	-	15	-	20	-	nS
Chip Selection to End of Write		T _{CW}	9	-	10	-	13	-	17	-	nS
Address Valid to End of Write		T _{AW}	9	-	10	-	13	-	17	-	nS
Address Setup Time		T _{AS}	0	-	0	-	0	-	0	-	nS
Write Pulse Width		T _{WP}	9	-	10	-	10	-	12	-	nS
Write Recovery Time	$\overline{\text{CS}}, \overline{\text{WE}}$	T _{WR}	0	-	0	-	0	-	0	-	nS
Data Valid to End of Write		T _{DW}	6	-	7	-	9	-	10	-	nS
Data Hold from End of Write		T _{DH}	0	-	0	-	0	-	0	-	nS
Write to Output in High Z		T _{WHZ} *	-	6	-	7	-	8	-	10	nS
Output Disable to Output in High Z		T _{OHZ} *	-	6	-	7	-	8	-	10	nS
Output Active from End of Write		T _{OW}	0	-	0	-	0	-	0	-	nS

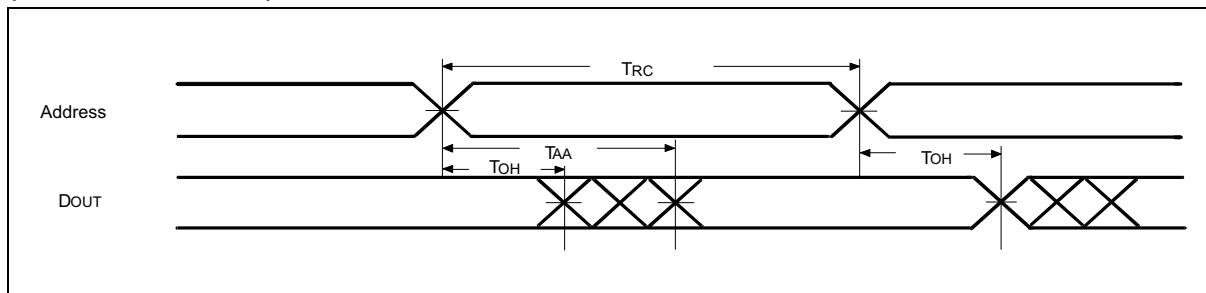
* These parameters are sampled but not 100% tested.



TIMING WAVEFORMS

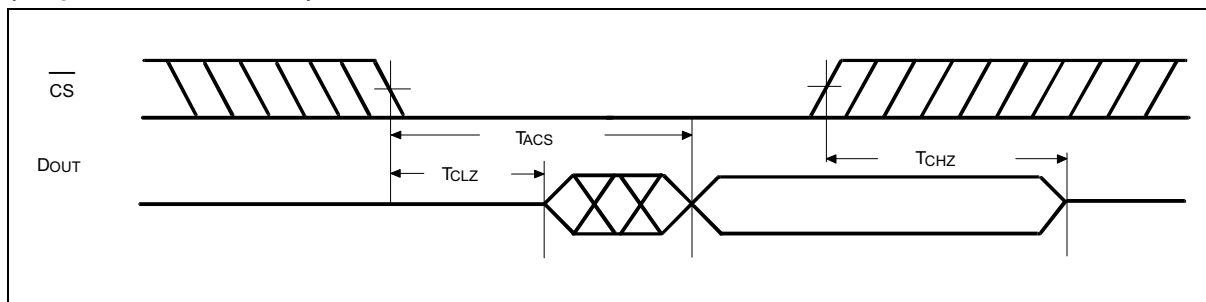
Read Cycle 1

(Address Controlled)



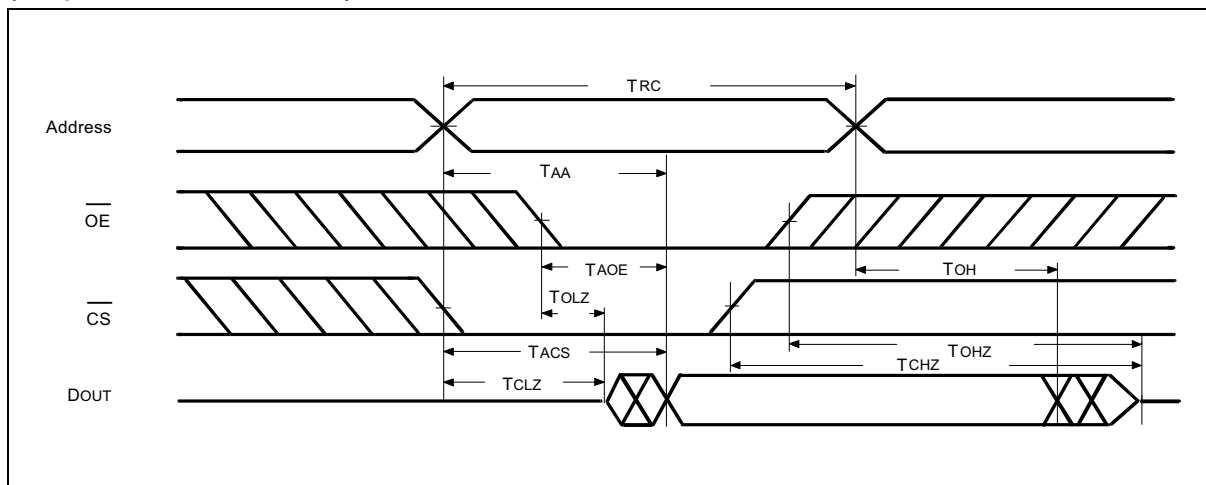
Read Cycle 2

(Chip Select Controlled)



Read Cycle 3

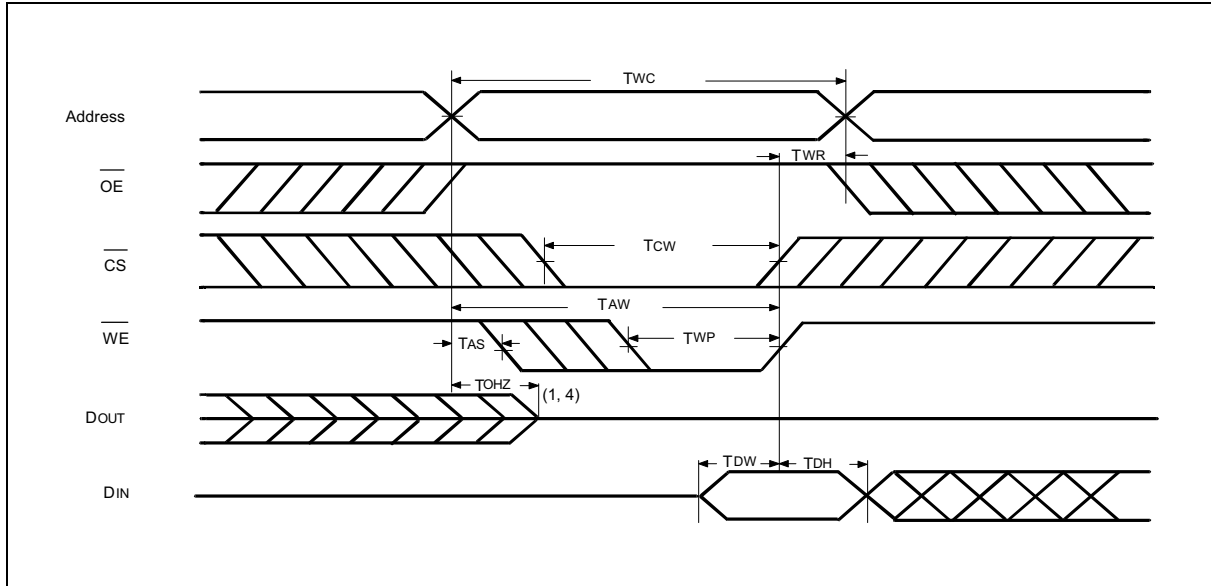
(Output Enable Controlled)



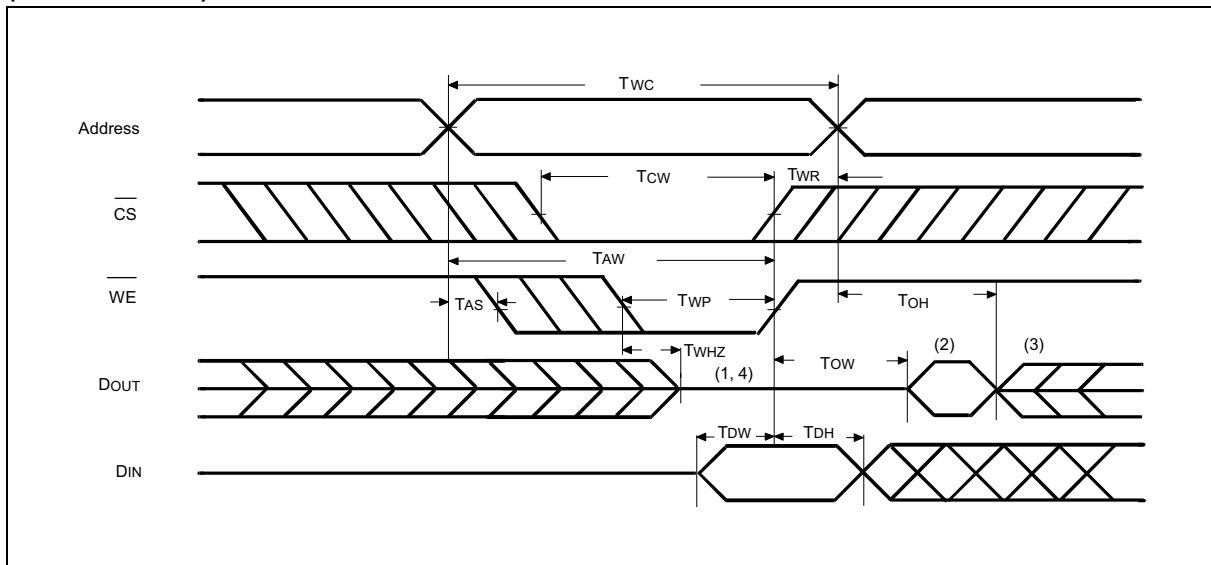


Timing Waveforms, continued

Write Cycle 1 (OE Clock)



Write Cycle 2 ($\overline{OE}$ = VIL Fixed)



Notes:

1. During this period, I/O pins are in the output state, so input signals of opposite phase to the outputs should not be applied.
2. The data output from DOUT are the same as the data written to DIN during the write cycle.
3. DOUT provides the read data for the next address.
4. Transition is measured ± 500 mV from steady state with $C_L = 5$ pF. This parameter is guaranteed but not 100% tested.

**ORDERING INFORMATION**

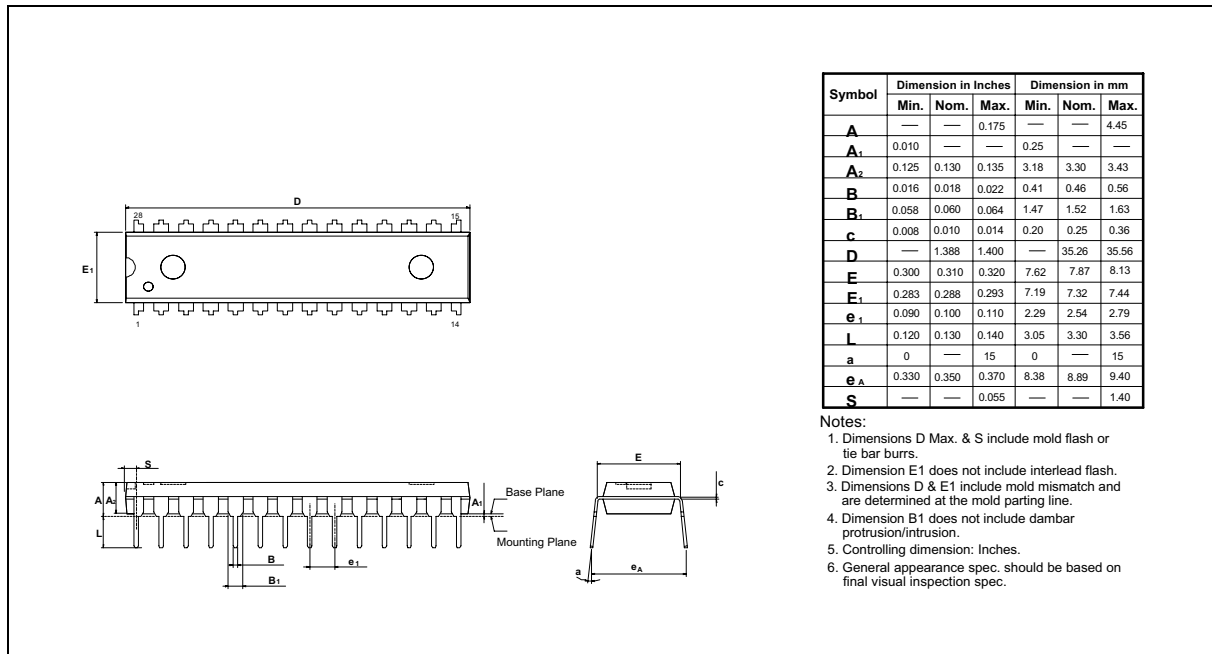
PART NO.	ACCESS TIME (nS)	OPERATING CURRENT MAX. (mA)	STANDBY CURRENT MAX. (mA)	PACKAGE
W24257AK-10	10	170	10	300 mil skinny DIP
W24257AK-12	12	160	10	300 mil skinny DIP
W24257AK-15	15	150	10	300 mil skinny DIP
W24257AK-20	20	140	10	300 mil skinny DIP
W24257AJ-10	10	170	10	300 mil SOJ
W24257AJ-12	12	160	10	300 mil SOJ
W24257AJ-15	15	150	10	300 mil SOJ
W24257AJ-20	20	140	10	300 mil SOJ
W24257AS-10	10	170	10	330 mil SOP
W24257AS-12	12	160	10	330 mil SOP
W24257AS-15	15	150	10	330 mil SOP
W24257AS-20	20	140	10	330 mil SOP
W24257AQ-10	10	170	10	Standard type one TSOP
W24257AQ-12	12	160	10	Standard type one TSOP
W24257AQ-15	15	150	10	Standard type one TSOP
W24257AQ-20	20	140	10	Standard type one TSOP

Notes:

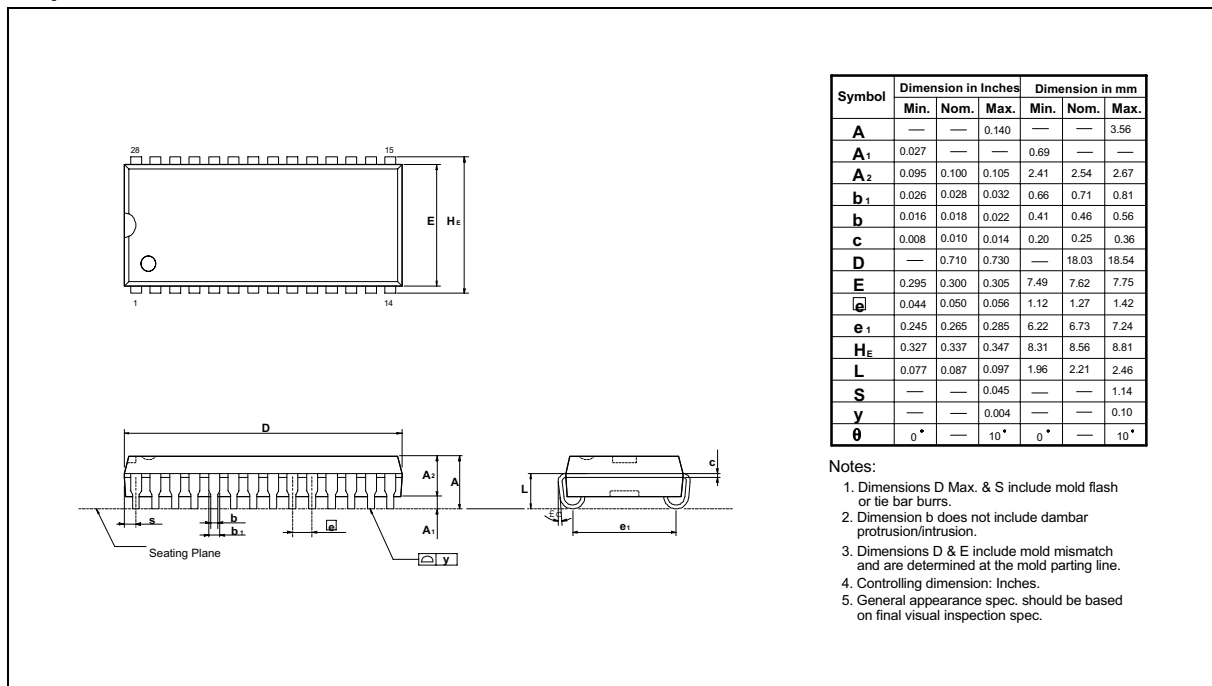
1. Winbond reserves the right to make changes to its products without prior notice.
2. Purchasers are responsible for performing appropriate quality assurance testing on products intended for use in applications where personal injury might occur as a consequence of product failure.

PACKAGE DIMENSIONS

28-pin P-DIP Skinny

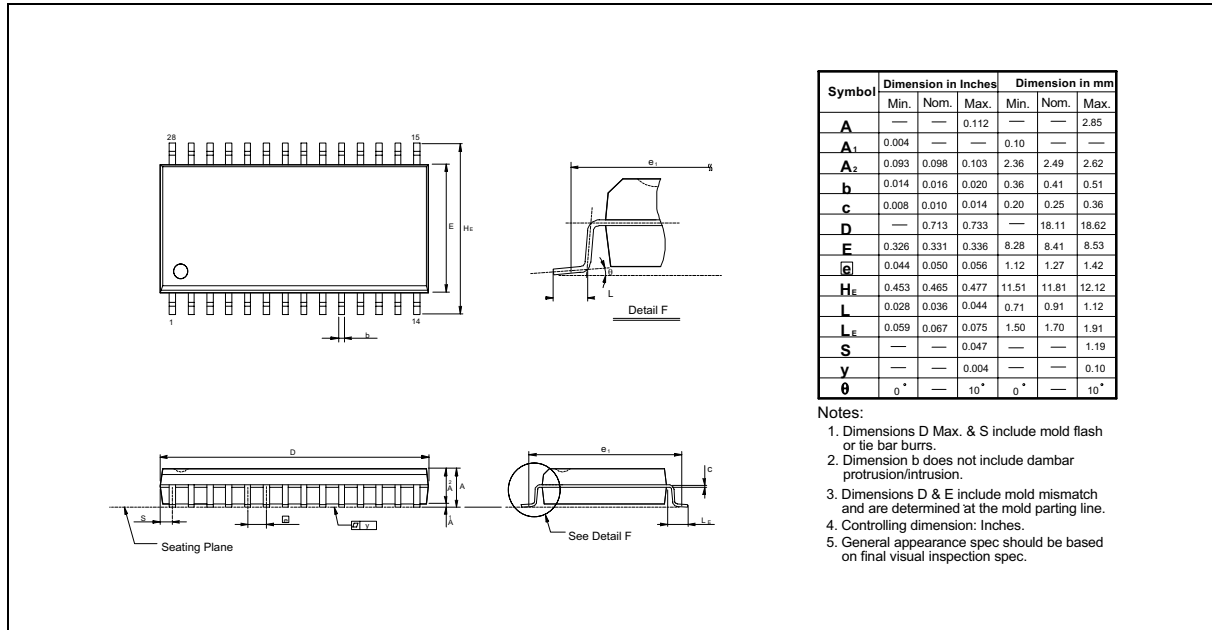


28-pin Small Outline J Band

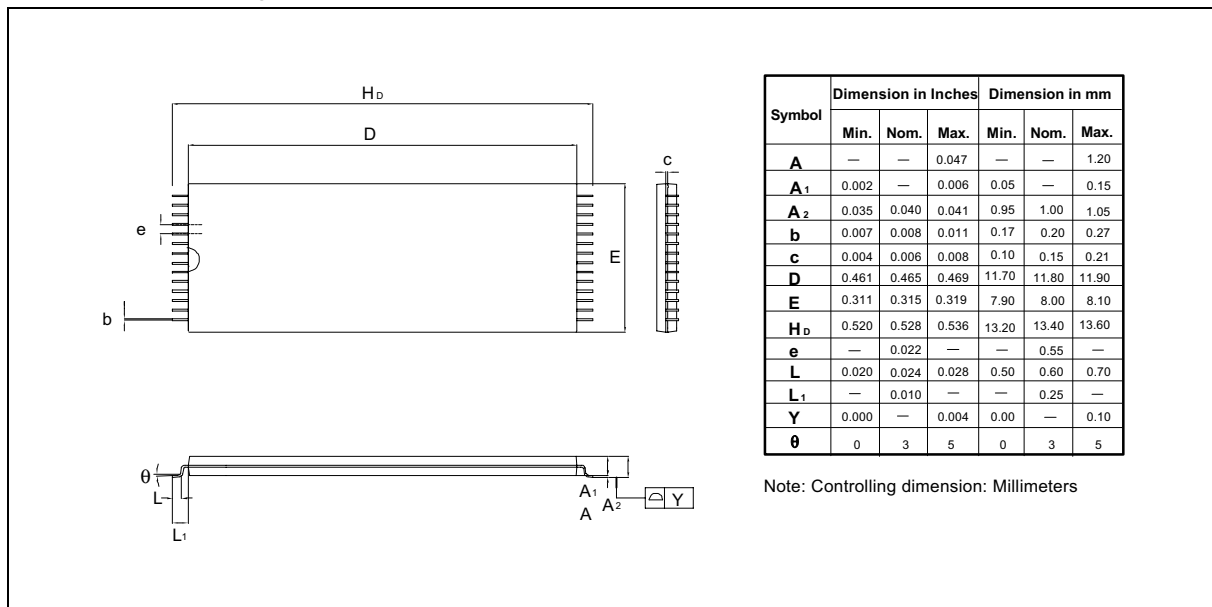


Package Dimensions, continued

28-pin SO Wide Body



28-pin Standard Type One TSOP



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Note: All data and specifications are subject to change without notice.